

Notice of References Cited	Application/Control No. 10/828,900		Applicant(s)/Patent Under Reexamination WARE, FREDERICK A.	
	Examiner Pierre-Michel Bataille		Art Unit 2186	Page 1 of 1

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*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
*	A	US-2005/0177675	08-2005	Newman et al.	711/005
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	K	US-			
	L	US-			
	M	US-			

FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
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NON-PATENT DOCUMENTS

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*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
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